INTEGRATED CIRCUITS



Product specification Supersedes data of 1995 Mar 21 File under Integrated Circuits, IC02 1996 Jun 10



FEATURES

- Balanced mixer with a common emitter input for band A (single input)
- 2-pin oscillator for bands A and B
- Balanced mixer with a common base input for bands B and C (balanced input)
- 4-pin oscillator for band C
- Local oscillator buffer output for external prescaler
- SAW filter preamplifier with a low output impedance to drive a 75 Ω load
- · Band gap voltage stabilizer for oscillator stability
- · Electronic band switch
- External IF filter between the mixer output and the IF amplifier input
- Pin to pin compatible with TDA5636B; TDA5637B family (same function with symmetrical IF output).

APPLICATIONS

- 3-band all-channel TV and VCR tuners
- Any standard.

GENERAL DESCRIPTION

The TDA5636 and TDA5637 are monolithic integrated circuits that perform the mixer/oscillator functions for bands A, B and C in TV and VCR tuners. These low-power mixer/oscillators require a power supply of 9 V and are available in a very small package.

The devices give the designer the capability to design an economical and physically small 3-band tuner.

They are suitable for European standards, as illustrated in Fig.17, with the following RF bands:

- 48.25 to 168.25 MHz
- 175.25 to 447.25 MHz
- 455.25 to 855.25 MHz.

With an appropriate tuned circuit, they are also suitable for NTSC all-channel tuners (USA and Japan). The tuner development time can be drastically reduced by using these devices.

These circuits belong to the TDA5636B/TDA5637B family which has exactly the same function with an IF amplifier having a symmetrical IF output to drive a SAW filter directly. It is possible to build tuners with either an asymmetrical or a symmetrical IF output with one main tuner lay-out.

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QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
VP	supply voltage		-	9.0	_	V
I _P	supply current	band A	-	45	_	mA
		band B	-	41	-	mA
		band C	-	44	-	mA
f _{RF}	frequency range	RF input; band A; note 1	45	-	180	MHz
		RF input; band B; note 1	160	-	470	MHz
		RF input; band C; note 1	430	-	860	MHz
G _v	voltage gain	band A; $R_L = 75 \Omega$	-	20	-	dB
		band B; $R_L = 75 \Omega$	-	31	-	dB
		band C; $R_L = 75 \Omega$	-	31	-	dB
NF	noise figure	band A; $R_L = 75 \Omega$	—	7.5	-	dB
		band B; $R_L = 75 \Omega$	-	6	-	dB
		band C; $R_L = 75 \Omega$	-	7	-	dB
Vo	output voltage to get 1% cross	band A; $R_L = 75 \Omega$	_	110	_	dBµV
	modulation in channel	band B; $R_L = 75 \Omega$	_	110	_	dBµV
		band C; $R_L = 75 \Omega$	—	110	-	dBµV

Note

1. The limits are related to the tank circuits used in Fig.17 and the intermediate frequency. Frequency bands may be adjusted by the choice of external components.

ORDERING INFORMATION

TYPE NUMBER		PACKAGE				
	NAME	DESCRIPTION	VERSION			
TDA5636T	SO24	plastic small outline package; 24 leads; body width 7.5 mm	SOT137-1			
TDA5636M	SSOP24	plastic shrink small outline package; 24 leads; body width 5.3 mm	SOT340-1			
TDA5637T	SO24	plastic small outline package; 24 leads; body width 7.5 mm	SOT137-1			
TDA5637M	SSOP24	plastic shrink small outline package; 24 leads; body width 5.3 mm	SOT340-1			

BLOCK DIAGRAM



PINNING

	Р	IN	DECODIDITION	
SYMBOL	TDA5636	TDA5637	DESCRIPTION	
CIN1	1	24	band C input 1	
CIN2	2	23	band C input 2	
RFGND	3	22	ground for RF inputs	
BIN1	4	21	band B input 1	
BIN2	5	20	band B input 2	
AIN	6	19	band A input	
V _P	7	18	supply voltage	
MIXOUT1	8	17	mixers output 1	
MIXOUT2	9	16	mixers output 2	
GND1	10	15	ground 1 (0 V)	
LOOUT1	11	14	local oscillator amplifier output 1	
LOOUT2	12	13	local oscillator amplifier output 2	
IFOUT	13	12	IF amplifier output	
IFGND	14	11	IF amplifier ground	
BS	15	10	electronic band switch input	
GND2	16	9	ground 2 (0 V)	
BOSCOC	17	8	band B oscillator output collector	
COSCIB1	18	7	band C oscillator input base 1	
BOSCIB	19	6	band B oscillator input base	
COSCOC1	20	5	band C oscillator output collector 1	
COSCOC2	21	4	band C oscillator output collector 2	
AOSCOC	22	3	band A oscillator output collector	
COSCIB2	23	2	band C oscillator input base 2	
AOSCIB	24	1	band A oscillator input base	

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9 V VHF, hyperband and UHF mixersoscillators for TV and VCR 3-band tuners

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _P	supply voltage	-0.3	+10.5	V
V _{SW}	switching voltage	0	10.5	V
I _O	output current of each pin to ground	-	-10	mA
t _{sc(max)}	maximum short-circuit time (all pins)	-	10	s
T _{stg}	IC storage temperature	-55	+150	°C
T _{amb}	operating ambient temperature	-10	+80	°C
Tj	junction temperature	-	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	TYPICAL VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient in free air		
	SSOP	120	K/W
	SO	75	K/W

HANDLING

Human Body Model

For TDA5636 GND (10, 16), RFGND (3), IFGND (14) and V_P (7) are separate. For TDA5637 GND (9, 15), RFGND (22), IFGND (11) and V_P (18) are separate.

All pins withstand 2000 V in accordance with the "UZW-BO/FQ-A302" specification equivalent to the "MIL-STD-883C" category B (2000 V).

Machine Model

All pins withstand 200 V in accordance with the "UZW-BO/FQ-B302 (issue date: Nov 6th, 1990)" specification.

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CHARACTERISTICS

 V_{P} = 9 V; T_{amb} = 25 °C; measured in circuit of Fig.17; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Supply			·	·	·	
V _P	supply voltage		8.1	9.0	9.9	V
I _P	supply current	band A	_	45	50.5	mA
		band B	-	41	46	mA
		band C	-	44	49	mA
V _{SW}	switching voltage	band A	0	-	1.1	V
		band B	1.6	-	2.4	V
		band C	3.0	-	V _P	V
I _{SW}	switching current	band A	_	-	2	μA
		band B	-	-	5	μA
		band C; V _{SW(C)} = 5 V	-	-	10	μA
Band A m	ixer (including IF am	plifier)	-1	-		
f _{RF}	frequency range	note 1	45	_	180	MHz
G _v	voltage gain	R_L = 75 Ω; f_{RF} = 50 MHz; see Fig.4	17.5	20.0	22.5	dB
		R_L = 75 Ω; f_{RF} = 180 MHz; see Fig.4	17.5	20.0	22.5	dB
NF r	noise figure	R_L = 75 Ω; f_{RF} = 50 MHz; see Figs 5 and 6.	-	7.5	9.5	dB
		$R_L = 75 \Omega$; f _{RF} = 180 MHz; see Figs 5 and 6.	-	7.5	9.5	dB
Vo	output voltage	1% cross-modulation in channel; R _L = 75 Ω ; f _{RF} = 50 MHz; see Fig.7	107	110	-	dBµV
		1% cross-modulation in channel; R _L = 75 Ω ; f _{RF} = 180 MHz; see Fig.7	107	110	-	dBµV
Vi	input voltage	10 kHz pulling in channel; f _{RF} = 180 MHz; note 6	-	100	-	dBµV
g _{os}	optimum source	f _{RF} = 50 MHz	_	0.5	-	mS
	conductance	f _{RF} = 180 MHz	_	1	_	mS
Y _i	input admittance	see Fig.12	_	-	-	mS
C _i	input capacitance	f _{RF} = 50 to 180 MHz; see Fig.12	_	2	_	pF
Band A os	scillator					1
fosc	frequency range	note 2	80	_	216	MHz
f _{shift}	frequency shift	$\Delta V_p = 10\%$; note 3	_	_	200	kHz
f _{drift}	frequency drift	$\Delta T = 25$ °C with no compensation; NP0 capacitors; note 4	-	-	600	kHz
		5 s to 15 min after switching on; note 5	_	_	200	kHz

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Band B m	ixer (including IF am	plifier)				
f _{RF}	frequency range	note 1	160	_	470	MHz
G _v	voltage gain	R _L = 75 Ω; f _{RF} = 170 MHz; see Fig.8	28	31	34	dB
		R_L = 75 Ω; f_{RF} = 470 MHz; see Fig.8	28	31	34	dB
NF	noise figure	R _L = 75 Ω; f _{RF} = 170 MHz; see Fig.9	-	6.0	8.0	dB
	(not corrected for image)	$R_L = 75 \Omega$; $f_{RF} = 470 \text{ MHz}$; see Fig.9	-	7.0	9.0	dB
Vo	output voltage	1% cross-modulation in channel; R _L = 75 Ω; f _{RF} = 170 MHz; see Fig.10	107	110	-	dBµV
		1% cross-modulation in channel; R _L = 75 Ω ; f _{RF} = 470 MHz; see Fig.10	107	110	-	dBµV
Vi	input voltage	10 kHz pulling in channel; f _{RF} = 470 MHz; note 6	-	91	-	dBµV
	input voltage	N + 5 – 1 MHz pulling; f _{RF} = 430 MHz; see Fig.11	-	77	-	dBµV
Z _i	input impedance	f _{RF} = 170 to 470 MHz; see Fig.13	_	30	_	Ω
	$(R_s + jL_s\omega)$	f _{RF} = 170 to 470 MHz; see Fig.13	-	10	_	nH
Band B os	scillator					
f _{OSC}	frequency range	note 2	200	-	500	MHz
f _{shift}	frequency shift	$\Delta V_P = 10\%$; note 3	-	-	400	kHz
f _{drift}	frequency drift	$\Delta T = 25$ °C with no compensation; NP0 capacitors; note 4	-	-	2	MHz
		5 s to 15 min after switching on; note 5	_	-	300	kHz
Band C m	ixer (including IF am	plifier)				•
f _{RF}	frequency range	note 1	430	_	860	MHz
Gv	voltage gain	R _L = 75 Ω; f _{RF} = 430 MHz; see Fig.8	28	31	34	dB
		$R_L = 75 \Omega$; $f_{RF} = 860 \text{ MHz}$; see Fig.8	28	31	34	dB
NF	noise figure	$R_L = 75 \Omega$; $f_{RF} = 430 \text{ MHz}$; see Fig.9	-	7.0	9.0	dB
	(not corrected for image)	$R_L = 75 \Omega$; $f_{RF} = 860 \text{ MHz}$; see Fig.9	-	8.0	10.0	dB
Vo	output voltage	1% cross-modulation in channel; R _L = 75 Ω ; f _{RF} = 430 MHz; see Fig.10	107	110	-	dBµV
		1% cross-modulation in channel; R _L = 75 Ω ; f _{RF} = 860 MHz; see Fig.10	107	110	-	dBµV
Vi	input voltage	10 kHz pulling in channel; f _{RF} = 860 MHz; note 6	-	93	-	dBµV
	input voltage	N + 5 – 1 MHz pulling; f _{RF} = 820 MHz; see Fig.11	-	79	-	dBµV
Zi	input impedance	f _{RF} = 430 to 860 MHz; see Fig.14	_	40	_	Ω
	$(R_s + jL_s\omega)$	f _{RF} = 430 to 860 MHz; see Fig.14	_	10	_	nH

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Band C os	scillator		ł		_	
f _{OSC}	frequency range	note 2	470	-	900	MHz
f _{shift}	frequency shift	$\Delta V_P = 10\%$; note 3	_	_	500	kHz
f _{drift} fr	frequency drift	$\Delta T = 25 \ ^{\circ}C$ with compensation; note 4	-	-	1400	kHz
		5 s to 15 min after switching on; note 5	-	-	400	kHz
LO output						
S ₂₂	output reflection coefficient	see Fig.16	-	-	-	
Y _O	output admittance	see Fig.16	_	400	-	Ω
(Y _p + jωC _p)	see Fig.16	_	0.7	_	pF	
Vo	output voltage	$R_L = 50 \Omega$	83	91	100	dBµV
SRF	spurious signal on LO output with respect to LO output signal	R _L = 50 Ω; note 7	-	-	-10	dBc
HLO	LO signal harmonics with respect to LO signal	R _L = 50 Ω	-	-	-10	dBc
IF amplifie	er		-			-
S ₂₂	output reflection	magnitude; through 1 nF; see Fig.15	-	-14.5	-	dB
	coefficient	phase; through 1 nF; see Fig.15	-	5.5	-	deg.
Zo	output impedance	R _S ; through 1 nF	_	73	_	Ω
	$(R_s + j\omega L_s)$	L _S ; through 1 nF	-	12	_	nH

Notes

- 1. The RF frequency range is defined by the oscillator frequency range and the intermediate frequency.
- 2. Limits are related to the tank circuits used in Fig.17; frequency bands may be adjusted by the choice of external components.
- 3. The frequency shift is defined as the change in oscillator frequency when the supply voltage varies from $V_P = 9$ to 8.1 V or from $V_P = 9$ to 9.9 V.
- 4. The frequency drift is defined as the change in oscillator frequency when the ambient temperature varies from $T_{amb} = 25$ to 0 °C or from $T_{amb} = 25$ to 50 °C.
- 5. Switching on drift is defined as the change in oscillator frequency between 5 s and 15 min after switching on.
- 6. The input level causing 10 kHz frequency detuning at the LO output; $f_{OSC} = f_{RF} + 38.9$ MHz.
- 7. SRF: spurious signal on LO with respect to LO output signal:

RF level = 120 dB μ V at f_{RF} < 180 MHz

RF level = 107.5 dB μ V at f_{RF} = 180 to 225 MHz

RF level = 97 dB μ V at f_{RF} = 225 to 860 MHz.















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Fig.11 N + 5 –1 MHz pulling measurement in bands B and C.











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APPLICATION INFORMATION



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Application diagram component values

Table 1 Capacitors

(all SMD and NP0 except C5 to C9 and C29)

NUMBER	VALUE
C1	2 pF
C2	2 pF
C3	82 pF
C4	2.2 nF
C5	1 pF (N750)
C6	1 pF (N750)
C7	1 pF (N750)
C8	1 pF (N750)
C9	6 pF (N470)
C10	100 pF
C11	2.2 nF
C12	2 pF
C13	4 pF
C14	150 pF
C15	2.2 nF
C16	1.2 nF
C17	1 nF
C18	1 nF
C19	1 nF
C20	12 pF
C21	12 pF
C22	22 nF
C23	1 nF
C24	1 nF
C25	1 nF
C26	1 nF
C27	1 nF
C28	2.2 nF
C29	1 μF (40 V electrolytic capacitor)

NUMBER	VALUE
R2	22 Ω
R3	47 kΩ
R4	2.2 kΩ
R5	22 kΩ
R6	47 kΩ
R7	47 kΩ
R8	12 Ω
R9	15 kΩ
R10	33 kΩ
R11	27 Ω
R12	100 Ω
R13	150 Ω
R14	47 kΩ

Table 3 Diodes, coils and transformers

Table 2 Resistors (all SMD)

NUMBER	VALUE
Diodes	
D1	BB132
D2	BB134
D3	BB146
Coils ⁽¹⁾	
L1	8 turns (Ø 3 mm)
L2	2 turns (Ø 2.5 mm)
L3	3 turns (Ø 2.5 mm)
L4	2 turns (Ø 4 mm)
Transformer ⁽²⁾	
L5	2×6 turns

Notes

- 1. Wire size for L1 to L4 is 0.4 mm.
- 2. Coil type: TOKO 7KN; material: 113 KN, screw core: 03-0093, pot core: 04-0026.

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INTERNAL PIN CONFIGURATION

	PIN			AVERAGE DC VOLTAGE ⁽¹⁾ IN (V)			
SYMBOL	TDA5636B	TDA5637B	DESCRIPTION	BAND A	BAND B	BAND C	
CIN1	1	24		0	0	2.2	
CIN2	2	23	(1) (24) (24) (23) MLD104	0	0	2.2	
RFGND	3	22	(22) MLD109	0	0	0	
BIN1	4	21		0	2.2	0	
BIN2	5	20	(21) (21) (20) <i>MLD103</i>	0	2.2	0	
AIN	6	19	(6) (19) (19) (10) (10) (10) (10) (10) (10)	2.2	1.2	1.2	
VP	7	18	supply voltage	9.0	9.0	9.0	
MIXOUT1	8	17	(17) (17) (16)	8.4	8.4	8.4	
MIXOUT2	9	16	MLD107	8.4	8.4	8.4	

SAMBOI	PIN		DECODIDION	AVERAGE DC VOLTAGE ⁽¹⁾ IN (V)			
SYMBOL	TDA5636B	TDA5637B	DESCRIPTION	BAND A	BAND B	BAND C	
GND1	10	15		0	0	0	
GND2	16	9	MLD106	0	0	0	
LOOUT1	11	14		5.6	5.6	5.6	
LOOUT2	12	13	MLD110	5.6	5.6	5.6	
IFOUT	13	12	MGD570 (12)	4.4	4.4	4.4	
IFGND	14	11	(14) (11) MBH476	0.0	0.0	0.0	
BS	15	10	(15) (10) MLD105	V _{SW(A)}	V _{SW(B)}	V _{SW(C)}	

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SYMBOL	PIN		DESCRIPTION	AVERAGE DC VOLTAGE ⁽¹⁾ IN (V)		
STMBOL	TDA5636B	TDA5637B	DESCRIPTION	BAND A	BAND B	BAND C
BOSCOC	17	8		5.8	3.4	5.8
BOSCIB	19	6		1.2	2.3	1.2
COSCIB1	18	7	¢ ¢	1.4	1.4	2.3
COSCOC1	20	5		5.8	5.8	4.2
COSCOC2	21	4		5.8	5.8	4.2
COSCIB2	23	2	↓ ↓ ↓ MLD112	1.4	1.4	2.3
AOSCOC	22	3		3.8	5.8	5.8
AOSCIB	24	1		2.1	1.0	1.0

Note

1. Average DC voltage measured in circuit of Fig.17.

PACKAGE OUTLINES



1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFERENCES				ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT137-1	075E05	MS-013AD				-95-01-24 97-05-22



SOLDERING

Introduction

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mounted components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mounted ICs, or for printed-circuits with high population densities. In these situations reflow soldering is often used.

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"IC Package Databook"* (order code 9398 652 90011).

Reflow soldering

Reflow soldering techniques are suitable for all SO and SSOP packages.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several techniques exist for reflowing; for example, thermal conduction by heated belt. Dwell times vary between 50 and 300 seconds depending on heating method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 °C.

Wave soldering

SO

Wave soldering techniques can be used for all SO packages if the following conditions are observed:

- A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.
- The longitudinal axis of the package footprint must be parallel to the solder flow.
- The package footprint must incorporate solder thieves at the downstream end.

SSOP

Wave soldering is **not** recommended for SSOP packages. This is because of the likelihood of solder bridging due to closely-spaced leads and the possibility of incomplete solder penetration in multi-lead devices.

If wave soldering cannot be avoided, the following conditions must be observed:

- A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.
- The longitudinal axis of the package footprint must be parallel to the solder flow and must incorporate solder thieves at the downstream end.

Even with these conditions, only consider wave soldering SSOP packages that have a body width of 4.4 mm, that is SSOP16 (SOT369-1) or SSOP20 (SOT266-1).

METHOD (SO AND SSOP)

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder is 10 seconds, if cooled to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Repairing soldered joints

Fix the component by first soldering two diagonallyopposite end leads. Use only a low voltage soldering iron (less than 24 V) applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

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DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limiting values				
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.				
Application information				
Where application information is given, it is advisory and does not form part of the specification.				

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

Product specification

9 V VHF, hyperband and UHF mixersoscillators for TV and VCR 3-band tuners

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NOTES

Philips Semiconductors – a worldwide company

Argentina: see South America Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113, Tel. +61 2 805 4455, Fax. +61 2 805 4466 Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 1 60 101. Fax. +43 1 60 101 1210 Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6, 220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773 Belgium: see The Netherlands Brazil: see South America Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor, 51 James Bourchier Blvd., 1407 SOFIA, Tel. +359 2 689 211, Fax. +359 2 689 102 Canada: PHILIPS SEMICONDUCTORS/COMPONENTS, Tel. +1 800 234 7381, Fax. +1 708 296 8556 China/Hong Kong: 501 Hong Kong Industrial Technology Centre, 72 Tat Chee Avenue, Kowloon Tong, HONG KONG, Tel. +852 2319 7888, Fax. +852 2319 7700 Colombia: see South America Czech Republic: see Austria Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S, Tel. +45 32 88 2636, Fax. +45 31 57 1949 Finland: Sinikalliontie 3, FIN-02630 ESPOO, Tel. +358 615 800, Fax. +358 615 80920 France: 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex, Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427 Germany: Hammerbrookstraße 69, D-20097 HAMBURG, Tel. +49 40 23 52 60, Fax. +49 40 23 536 300 Greece: No. 15, 25th March Street, GR 17778 TAVROS, Tel. +30 1 4894 339/911, Fax. +30 1 4814 240 Hungary: see Austria India: Philips INDIA Ltd, Shivsagar Estate, A Block, Dr. Annie Besant Rd. Worli, MUMBAI 400 018, Tel. +91 22 4938 541, Fax. +91 22 4938 722 Indonesia: see Singapore Ireland: Newstead, Clonskeagh, DUBLIN 14, Tel. +353 1 7640 000. Fax. +353 1 7640 200 Israel: RAPAC Electronics, 7 Kehilat Saloniki St, TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 648 1007 Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3, 20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557 Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108, Tel. +81 3 3740 5130, Fax. +81 3 3740 5077 Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL, Tel. +82 2 709 1412, Fax. +82 2 709 1415 Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR, Tel. +60 3 750 5214, Fax. +60 3 757 4880 Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905, Tel. +1 800 234 7381. Fax. +1 708 296 8556 Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB, Tel. +31 40 27 83749, Fax. +31 40 27 88399 New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND, Tel. +64 9 849 4160, Fax. +64 9 849 7811 Norway: Box 1, Manglerud 0612, OSLO, Tel. +47 22 74 8000, Fax. +47 22 74 8341 Philippines: Philips Semiconductors Philippines Inc., 106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI, Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474 Poland: UI. Lukiska 10, PL 04-123 WARSZAWA, Tel. +48 22 612 2831, Fax. +48 22 612 2327 Portugal: see Spain Romania: see Italy Russia: Philips Russia, UI. Usatcheva 35A, 119048 MOSCOW, Tel. +7 095 926 5361, Fax. +7 095 564 8323 Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231, Tel. +65 350 2538, Fax. +65 251 6500 Slovakia: see Austria Slovenia: see Italy South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale, 2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000, Tel. +27 11 470 5911, Fax. +27 11 470 5494 South America: Rua do Rocio 220 - 5th floor, Suite 51, CEP: 04552-903-SÃO PAULO-SP, Brazil, P.O. Box 7383 (01064-970), Tel. +55 11 821 2333, Fax. +55 11 829 1849 Spain: Balmes 22, 08007 BARCELONA Tel. +34 3 301 6312, Fax. +34 3 301 4107 Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM, Tel. +46 8 632 2000, Fax. +46 8 632 2745 Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH, Tel. +41 1 488 2686, Fax. +41 1 481 7730 Taiwan: PHILIPS TAIWAN Ltd., 23-30F, 66 Chung Hsiao West Road, Sec. 1, P.O. Box 22978, TAIPEI 100, Tel. +886 2 382 4443, Fax. +886 2 382 4444 Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd., 209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260, Tel. +66 2 745 4090, Fax. +66 2 398 0793 Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL, Tel. +90 212 279 2770, Fax. +90 212 282 6707 Ukraine: PHILIPS UKRAINE, 2A Akademika Koroleva str., Office 165, 252148 KIEV, Tel. +380 44 476 0297/1642, Fax. +380 44 476 6991 United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes, MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax, +44 181 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409, Tel. +1 800 234 7381, Fax. +1 708 296 8556 Uruguay: see South America

Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD, Tel. +381 11 825 344, Fax.+381 11 635 777

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